



SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOT-23 封装半导体二极管/SOT-23 Plastic-Encapsulate Diodes

BAT54&BAT54A&BAT54C&BAT54S

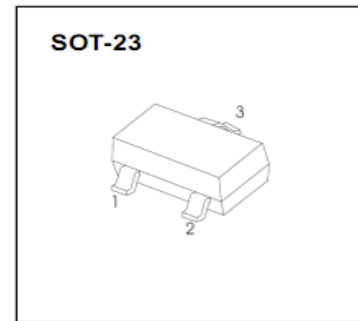
(SCHOTTKY DIODES)

特点/Features :

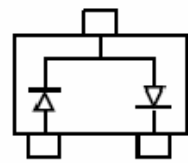
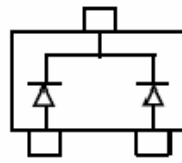
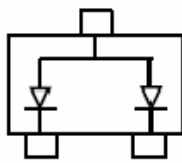
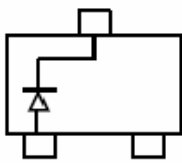
速度快，导通电压低；

用途/Applications :

高速开关电路。



电路和印章/Circuit&Marking:



BAT54 MARKING: KL1

BAT54A MARKING: KL2

BAT54C MARKING: KL3

BAT54S MARKING: KL4

极限参数/Absolute maximum ratings(Ta=25°C)

参数/Parameter	符号/ Symbol	数值/Value	单位/Unit
反向峰值电压/Peak Repetitive Peak Reverse Voltage	V_{RRM}	30	V
反向工作电压/Working Peak Reverse Voltage	V_{RWM}		
直流阻断电压/DC Blocking Voltage	V_R		
正向电流/Forward Continuous Current	I_F	200	mA
功率/ Power Dissipation	P_D	0.225	W
储存温度/Storage Temperature	T_{stg}	-55~150	°C

电性能参数/Electrical characteristics (Ta=25°C)

参数/Parasmeter	符号	测试条件	最小值	最大值	单位
反向击穿电压/Reverse Breakdown Voltage	$V_{R(BR)}$	$I_R=100 \mu A$	30		V
正向电压/Forward Voltage	V_{F1}	$I_F=0.1mA$		0.24	V
	V_{F2}	$I_F=1mA$		0.32	V
	V_{F3}	$I_F=10mA$		0.4	V
	V_{F4}	$I_F=30mA$		0.5	V
	V_{F5}	$I_F=100mA$		1	V
反向漏电流/Reverse Current	I_R	$V_R=25V$		2	μA
端电容/Capacitance Between Terminals	C_T	$V_R=1V, f=1MHz$		10	pF
反向恢复时间/Reverse Recovery Time	t_{rr}	$I_F=I_R=10mA,$ $I_{rr}=0.1 \times I_R,$ $R_L=100 \Omega$		5	nS



典型特性曲线图/Typical Characteristics

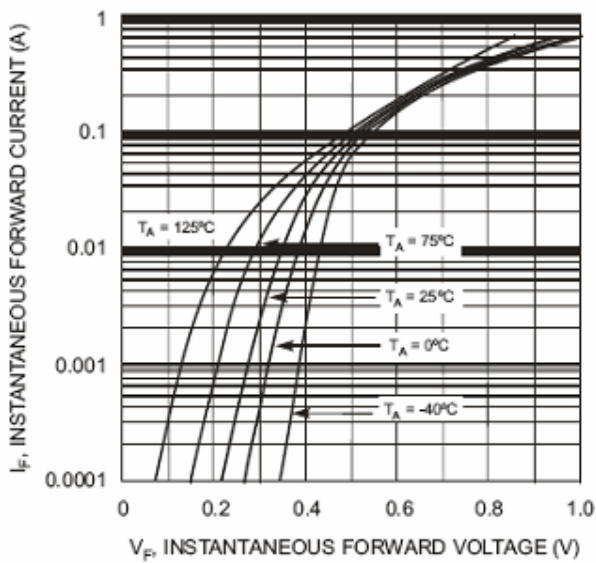


Fig. 1 Forward Characteristics

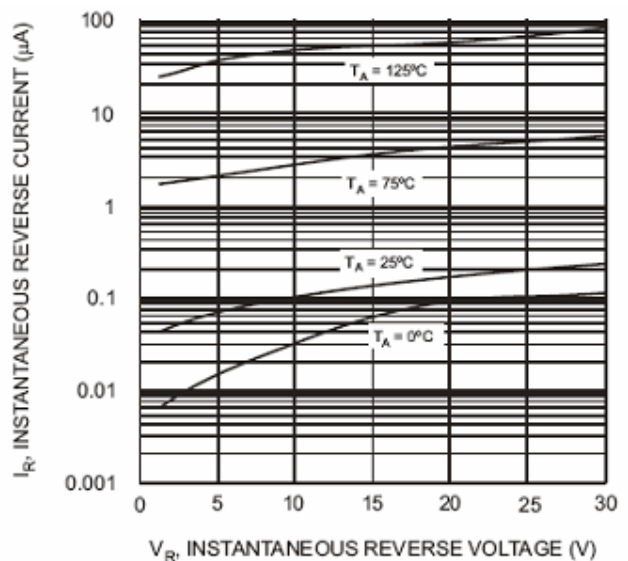


Fig. 2 Typical Reverse Characteristics

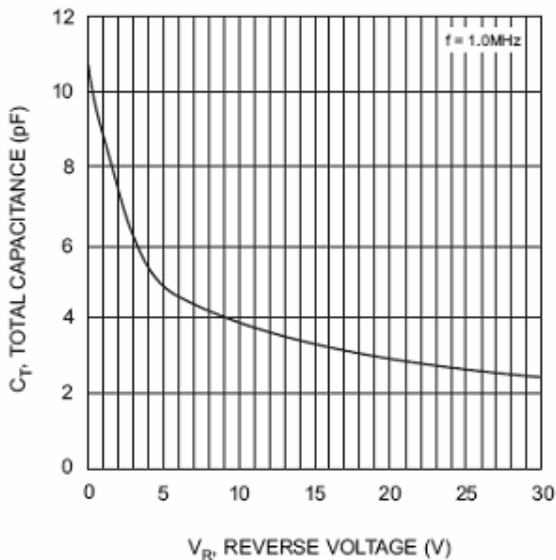


Fig. 3 Typical Capacitance vs. Reverse Voltage

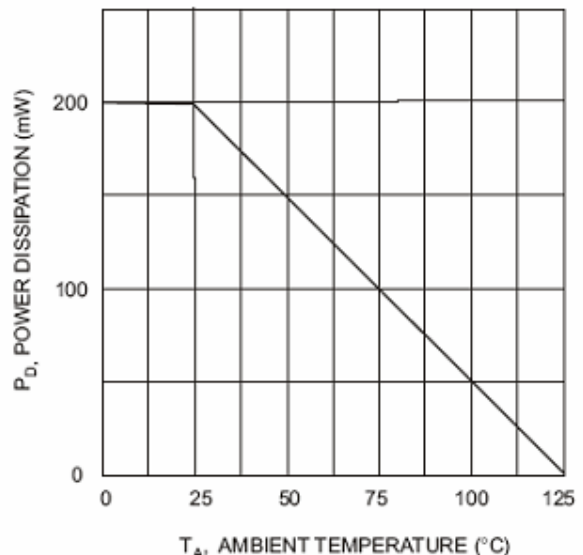


Fig. 4 Power Derating Curve